

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent Number: 7,880,117
Issued: February 1, 2011
Name of Patentee: Ming Li and Mitsuhiro Kimoto
Title of Invention: METHOD AND APPARATUS OF DRILLING HIGH DENSITY SUBMICRON CAVITIES USING PARALLEL LASER BEAMS

**REQUEST FOR CERTIFICATE OF CORRECTION OF PATENT
FOR PTO MISTAKE (37 C.F.R. § 1.322(a))**

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Attention: Decision and Certificate of Correction
Branch of the Patent Issue Division

1. Attached is Form PTO/SB/44.
2. Correction of the Official Letters Patent is respectfully requested in view of the following text which appears correctly in the application file:

The following foreign references were omitted from the face of the patent.

JP 2000-1766669	06/2000
JP 362057788A	03/1987
JP 401289586A	11/1989
JP 410048529A	02/1998
JP 411079791A	03/1999

The following non-patent literature documents were also omitted from the face of the patent.

Ming Li et al., "Nanostructuring In Submicron-Level Waveguides With Femtosecond Laser Pulses" Optics Communications, (2002), pp. 1-5 (Sept. 10, 2002).

Ming Li et al., "Femtosecond Laser Micromachining of Si-on-SiO₂ For Photonic Band Gap Crystal Fabrication", Jpn. J. Appl. Phys. Vol. 40 (2001), pp. 3476-3477, Part 1, No. 5A, May 2001.

3. Please send the Certificate to:

Kenneth N. Nigon
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610-407-0700

Respectfully submitted,



Kenneth N. Nigon, Reg. No. 31,549
Attorney for Applicant

KNN/ems

Enclosure: Form PTO/SB/44

Dated: February 9, 2011

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**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**

PATENT NO: 7,880,117

Page 1 of 1

APPLICATION NO.: 10/812,113

ISSUE DATE: February 1, 2011

INVENTOR(S): Ming Li, Mitsuhiro Kimoto

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

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This collection of information is required by 37 CFR 1.322, 1.323 and 1.324. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 1.0 hour to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Attention Certificate of Corrections Branch, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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